

Schottky barrier diode

RB548W

●Application

Rectifying small power

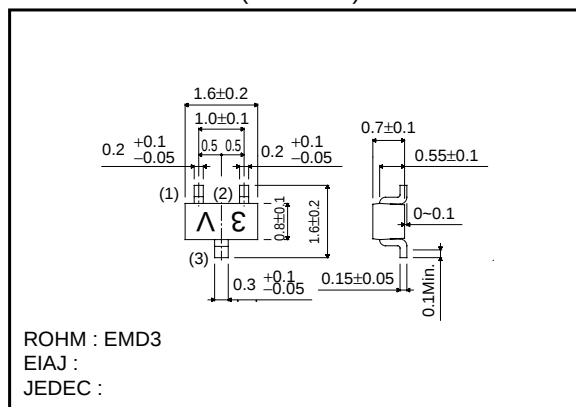
●Features

- 1) Extra small mold type. (EMD3)
- 2) High reliability.

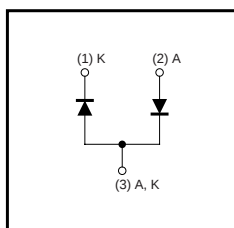
●Construction

Silicon epitaxial planer

●External dimensions (Units : mm)



●Circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current *1	I_o	100	mA
Forward current surge peak *2	I_{FSM}	0.5	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

*1 Rating of per diode

*2 60Hz, 1cyc. Rating of per diode

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.450	V	$I_F=10\text{mA}$
Reverse current	I_R	—	—	0.5	μA	$V_R=10\text{V}$

*Please pay attention to static electricity when handling.

●Electrical characteristic curves (Ta=25°C)

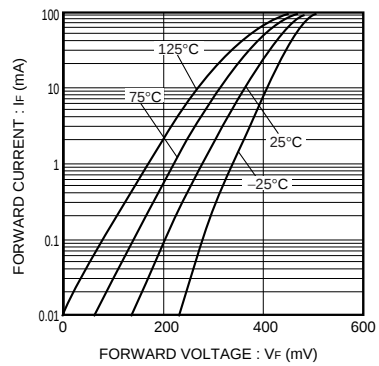


Fig. 1 Forward characteristics

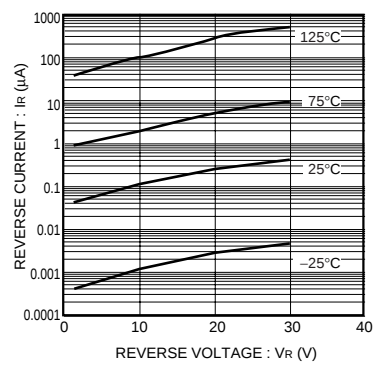


Fig. 2 Reverse characteristics

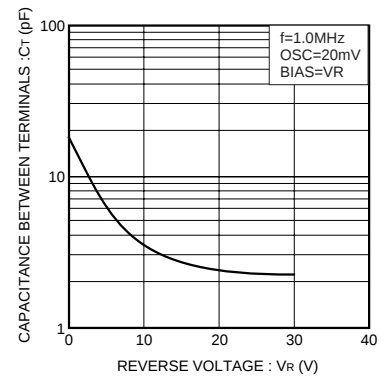


Fig. 3 Capacitance between terminals characteristics